

• General Description

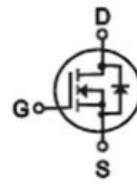
The ZM280N06S combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

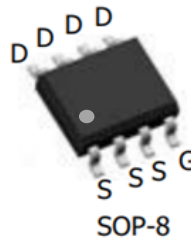
- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

• Product Summary


$V_{DS}=60V$

$R_{DS(ON)} = 28m\Omega$

$I_D=7A$


• Ordering Information:

Part NO.	ZM280N06S
Marking	ZM280N06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	7	A
	$I_D @ T_C = 75^\circ C$	5.3	A
	$I_D @ T_C = 100^\circ C$	4.4	A
Pulsed Drain Current ①	I_{DM}	15	A
Total Power Dissipation	$P_D @ T_C = 25^\circ C$	4.0	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	0.75	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	55	mJ

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	32	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	170	$^{\circ}C/W$
Soldering temperature, wave soldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=6A$		28	36	m Ω
		$V_{GS}=4.5V, I_D=4A$		33	43	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=5A$		14		s
Source-drain voltage	V_{SD}	$I_S=6A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	1430	-	pF
Output capacitance	C_{oss}		-	160	-	
Reverse transfer capacitance	C_{rss}		-	115	-	

•Gate Charge characteristics($T_a = 25^{\circ}C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$ $I_D = 4A$ $V_{GS} = 10V$	-	19	-	nC
Gate - Source charge	Q_{gs}		-	9	-	
Gate - Drain charge	Q_{gd}		-	11	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Power Dissipation

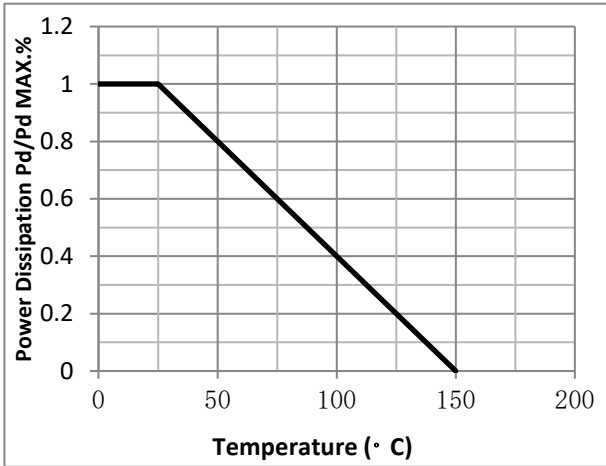


Fig.2 Typical output Characteristics

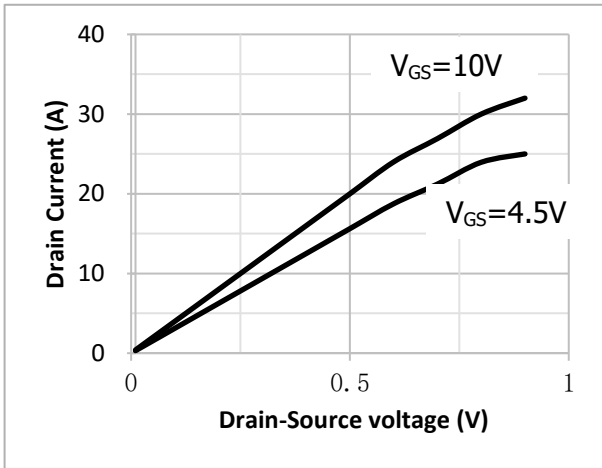


Fig.3 Threshold Voltage V.S Junction Temperature

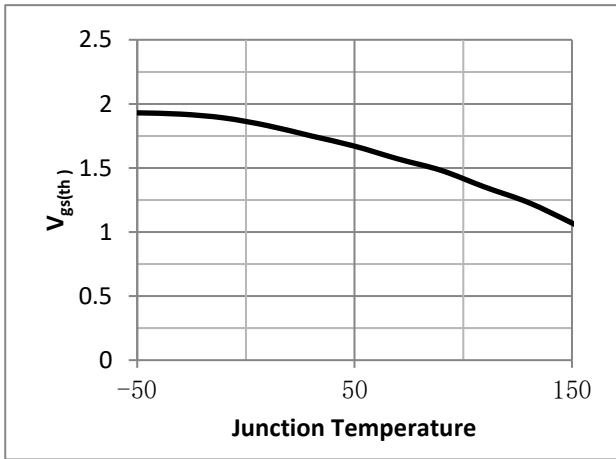


Fig.4 Resistance V.S Drain Current

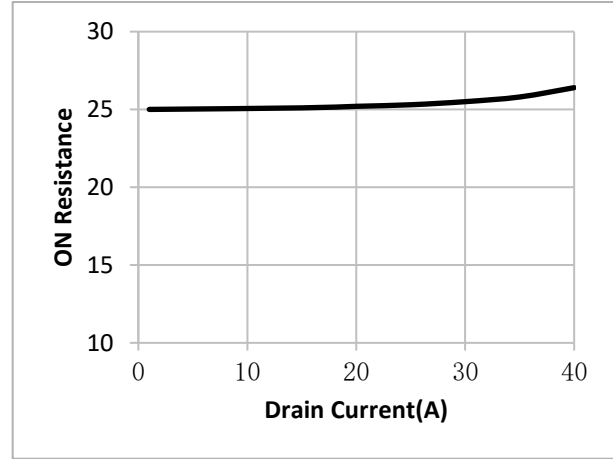


Fig.5 On-Resistance VS Gate Source Voltage

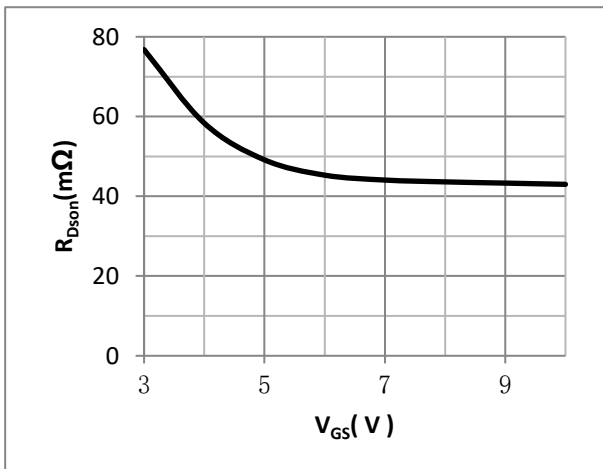


Fig.6 On-Resistance V.S Junction Temperature

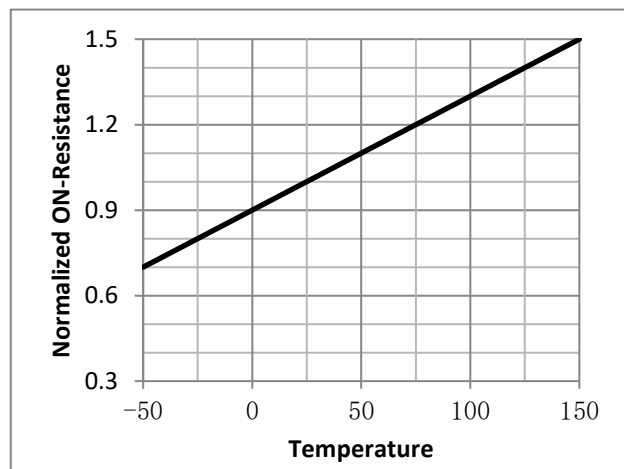


Fig.7 Switching Time Measurement Circuit

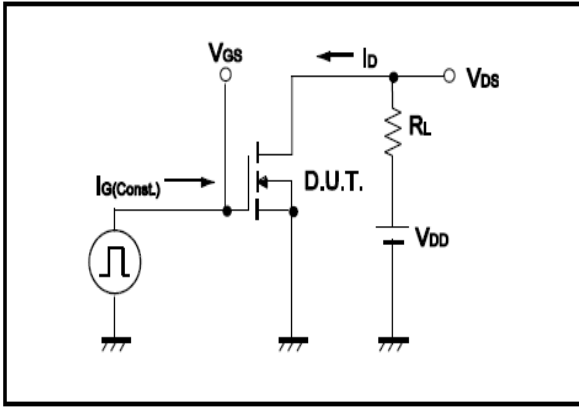


Fig.8 Gate Charge Waveform

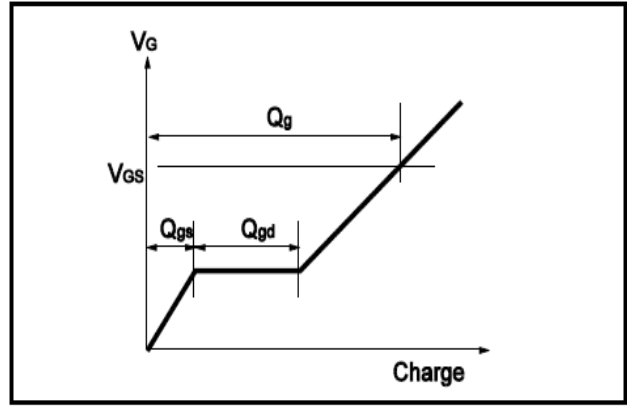


Fig.9 Switching Time Measurement Circuit

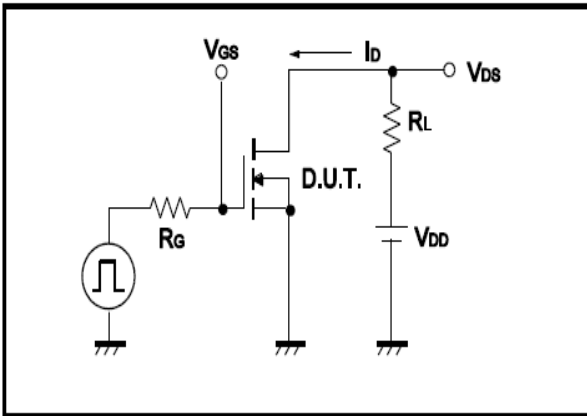


Fig.10 Gate Charge Waveform

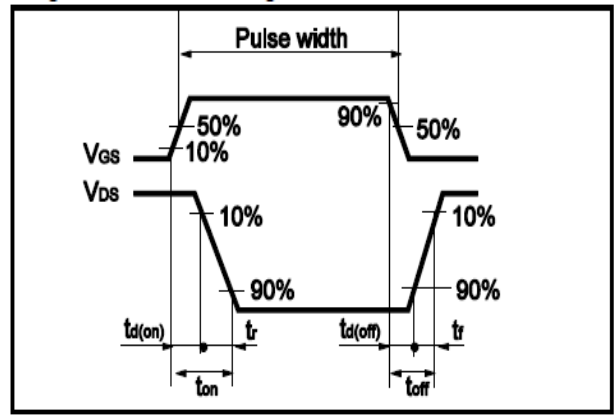


Fig.11 Avalanche Measurement Circuit

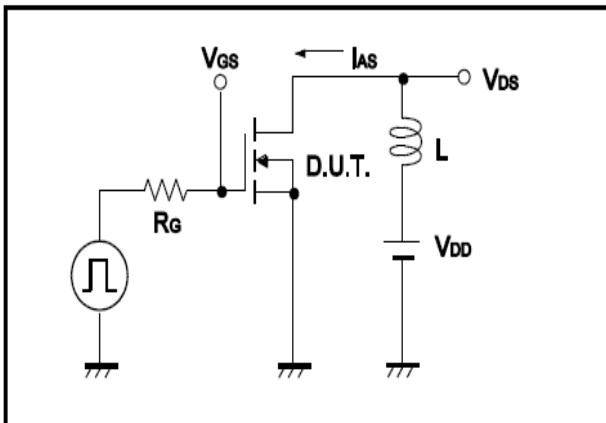
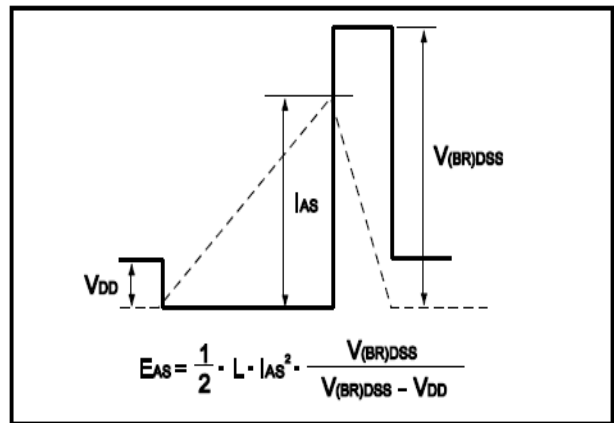


Fig.12 Avalanche Waveform



●Dimensions(SOP8)

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.10	0.20	0.23
B1	3.80		4.10	D		1.05	
B2		5.00		D1	0.40		0.62

